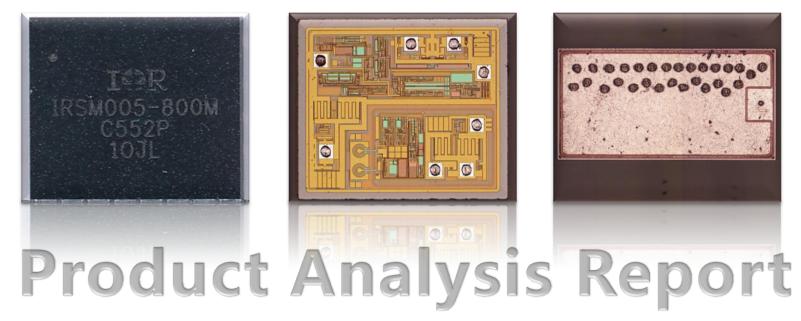


IRSM005-800MH

Half-Bridge IPM for Low Voltage Applications



This report is protected by copyright and may not be by way of trade or otherwise,be copied,reproduced,re-sold,lent,hired out in any form without express written permission from Shanghai Industrial µTechnology Research Institute(Hereinafter referred to as SITRI).SITRI always endeavors to provide accurate and reliable information to its customers. However, it is not possible to guarantee absolute accuracy of all information contained herein and SITRI can assume no liability for inadvertent errors in this report.

This report was prepared for our Clients' private study, analysis or research and for no other purpose. The information contained in this report may describe technical innovations, which are the subject of patents held by third parties. The disclosure by SITRI of any such information is in no form whatsoever an inducement to infringe any patent. SITRI assumes no liability for patent infringement arising from the use of the information contained in this report.



www.sitrigroup.com



Wechat



Table of Contents



Table 1 IRSM005-800MH Device Summary Figure 1.1.1 Package OM Photo Figure 1.2.1 Package X-Ray Photo Figure 1.3.1 Package CT Photo-PCB1 Figure1.3.2 Package CT Photo-PCB2 Figure 1.4.1 Package Pin Definition Figure 1.5.1 Package Internal Electrical Schematic correlated with Package Pin Definition Figure 2.1.1 IRSM005-800MH MOSFET Die1 Photo with Dimensions Figure 2.1.2 IRSM005-800MH MOSFET Die1 Corner Figure 2.1.3 IRSM005-800MH MOSFET Die1 Pad Size with Dimensions Figure 2.2.1 IRSM005-800MH MOSFET Die 2 Photo with Dimensions Figure 2.3.1 IRSM005-800MH Gate Driver IC Die Photo with Dimensions Figure 2.3.2 IRSM005-800MH Gate Driver IC Die Corner Figure 2.3.3 IRSM005-800MH Gate Driver IC Die Mark Figure 2.3.4 IRSM005-800MH Gate Driver IC Die Pad Size Figure 3.1.1 SEM Cross Section Image with Dimension-Die Thickness Figure 3.1.2 SEM Cross Section Image with Dimension-Metal Al Figure 3.1.3 SEM Cross Section Image with Dimensions-Trench Figure 3.1.4 SEM Cross Section Image with Horizontal Dimensions Figure 3.1.5 SEM Cross Section Image with Vertical Dimensions Figure 3.1.6 SEM Cross Section Image with Dimensions-Top Trench Figure 3.1.7 SEM Cross Section Image with Dimensions-Middle Trench Figure 3.1.8 SEM Cross Section Image with Dimensions-Bottom Trench Figure 4.1.1 SEM Cross Section Image with Body Description-After Stained

Figure 4.1.2 SEM Cross Section Image with P Body Dimension-After Stained Figure 4.1.3 SEM Cross Section Image with P+ Contact Implant Dimension-After Stained Figure 5.1.1 EDS Analysis in Cell Area Figure 5.1.2 EDS Analysis of Metal-Al Figure 5.1.3 EDS Analysis of Barrier Metal-TiN Figure 5.1.4 EDS Analysis of ILD2 Figure 5.1.5 EDS Analysis of ILD1 Figure 5.1.6 EDS Analysis of Trench Poly Figure 5.1.7 EDS Analysis of Gate Oxide Figure 6.1.1 Die Edge Guard Ring OM Image with Descriptions-After Stained Figure6.2.1 Die Edge Guard Ring SEM Image with Dimensions-After Stained Figure 6.2.2 Die Edge Guard Ring SEM Image After Stained with N- Epi Dimension Figure 6.2.3 Die Edge Guard Ring SEM Image After Stained with P Body Dimension Figure 6.2.4 Die Edge Guard Ring SEM Image After Stained with Dimension-Area1&2 Figure 6.2.5 Die Edge Guard Ring SEM Image After Stained with Dimension1-Area2 Figure 6.2.6 Die Edge Guard Ring SEM Image After Stained with Dimensions2-Area2 Figure 6.2.7 Die Edge Guard Ring SEM Image After Stained with Dimensions3-Area2 Figure 6.2.8 Die Edge Guard Ring SEM Image After Stained with Dimension1-Edge Figure 6.2.9 Die Edge Guard Ring SEM Image After Stained with Dimension2-Edge Figure 6.2.10 Die Edge Guard Ring SEM Image After Stained with Dimensions 3-Edge Figure 6.2.11 Die Edge Guard Ring SEM Image After Stained with Dimension1-Field Stop Figure 6.2.12 Die Edge Guard Ring SEM Image After Stained with Dimensions2-Field Stop Figure6.2.13 Die Edge Guard Ring SEM Image After Stained with Dimension3-Field Stop **Points**